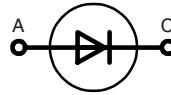
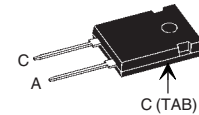
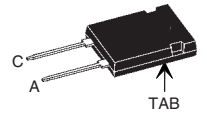


# HiPerFRED™ Epitaxial Diode

## with soft recovery

$I_{FAV} = 30 \text{ A}$   
 $V_{RRM} = 1200 \text{ V}$   
 $t_{rr} = 40 \text{ ns}$

$V_{RSM}$ V	$V_{RRM}$ V	Type
1200	1200	DSEP 30-12A
1200	1200	DSEP 30-12AR


**TO-247 AD**  
Version A

**ISOPLUS 247™**  
Version AR


A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$	rectangular, $d = 0.5$ ; $T_C$ (Vers. A) = 115°C $T_C$ (Vers. AR) = 110°C	70	A
$I_{FAVM}$		30	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	200	A
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 11.5 \text{ A}$ ; $L = 180 \mu\text{H}$	14	mJ
$I_{AR}$	$V_A = 1.25 \cdot V_R$ typ.; $f = 10 \text{ kHz}$ ; repetitive	1.2	A
$T_{VJ}$		-55...+175	°C
$T_{VJM}$		175	°C
$T_{stg}$		-55...+150	°C
$P_{tot}$	$T_C = 25^\circ\text{C}$	165	W
$M_d^*$	mounting torque	0.8...1.2	Nm
$F_C$	mounting force with clip	20...120	N
$V_{ISOL}^{**}$	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$ ; leads-to-tab	2500	V~
<b>Weight</b>	typical	6	g

\* Version A only; \*\* Version AR only

### Features

- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Version ..R isolated and UL registered E153432

### Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Dimensions see Outlines.pdf

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ ; $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ ; $V_R = V_{RRM}$	250 1	$\mu\text{A}$ mA
$V_F$ ②	$I_F = 30 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.79 2.74	V V
$R_{thJC}$	Version A Version AR	0.9 1.1	K/W K/W
$R_{thCH}$	0.25		K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 200 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	40	ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 50 \text{ A}$ ; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	8.5 11.4	A A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%

② Pulse Width = 300  $\mu\text{s}$ , Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.

IXYS reserves the right to change limits, test conditions and dimensions.

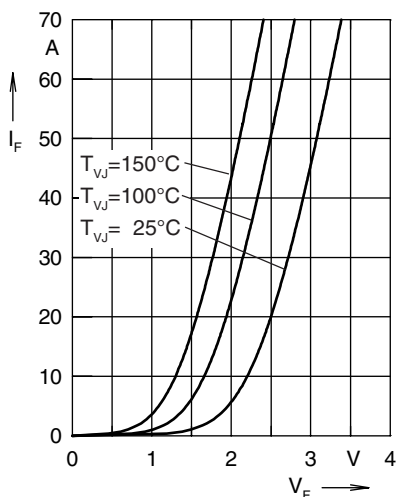


Fig. 1 Forward current  $I_F$  versus  $V_F$

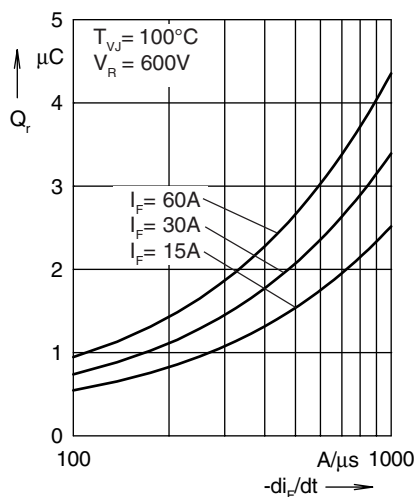


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

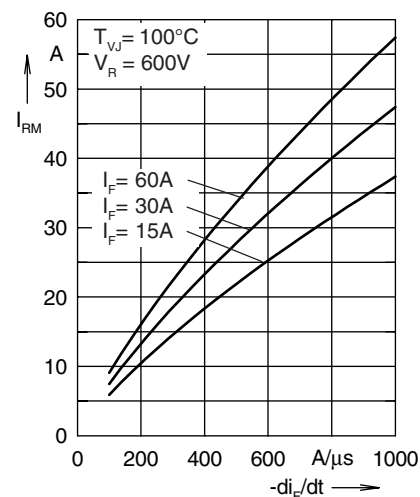


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

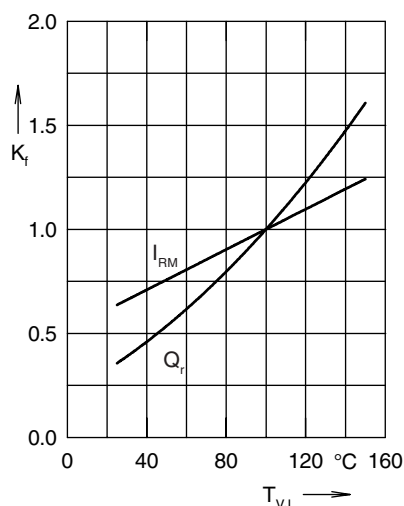


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

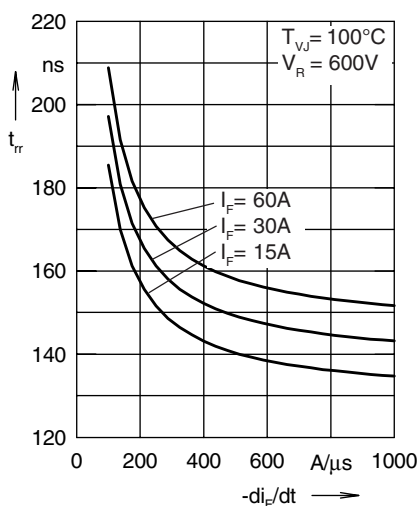


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$

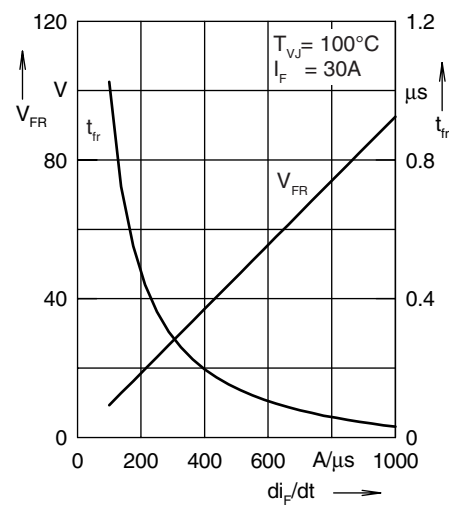


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

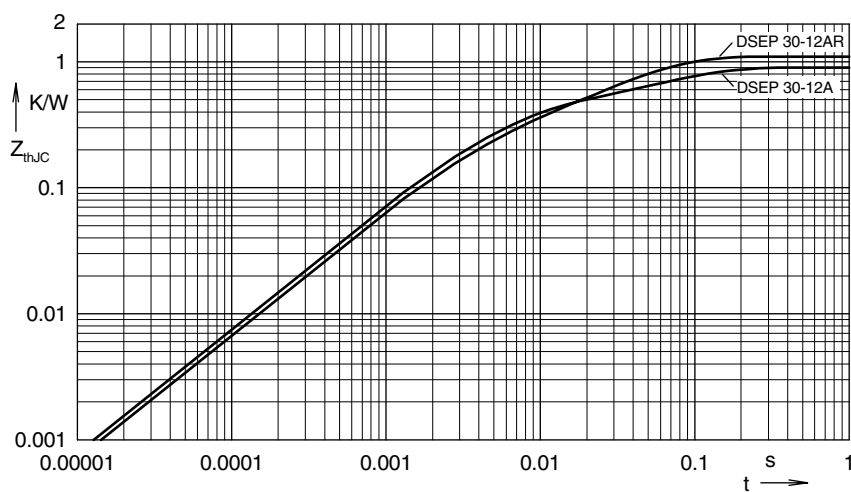


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation ..A:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.465	0.0052
2	0.179	0.0003
3	0.256	0.0397

Constants for  $Z_{thJC}$  calculation ..AR:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.368	0.0052
2	0.1417	0.0003
3	0.0295	0.0004
4	0.5604	0.0092

NOTE: Fig. 2 to Fig. 6 shows typical values